

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
30 June 2005 (30.06.2005)

PCT

(10) International Publication Number
WO 2005/060006 A2

(51) International Patent Classification⁷: **H01L 29/51**,
21/28, 21/316

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(21) International Application Number:
PCT/JP2004/019467

(22) International Filing Date:
17 December 2004 (17.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-421655 18 December 2003 (18.12.2003) JP
2004-219192 27 July 2004 (27.07.2004) JP

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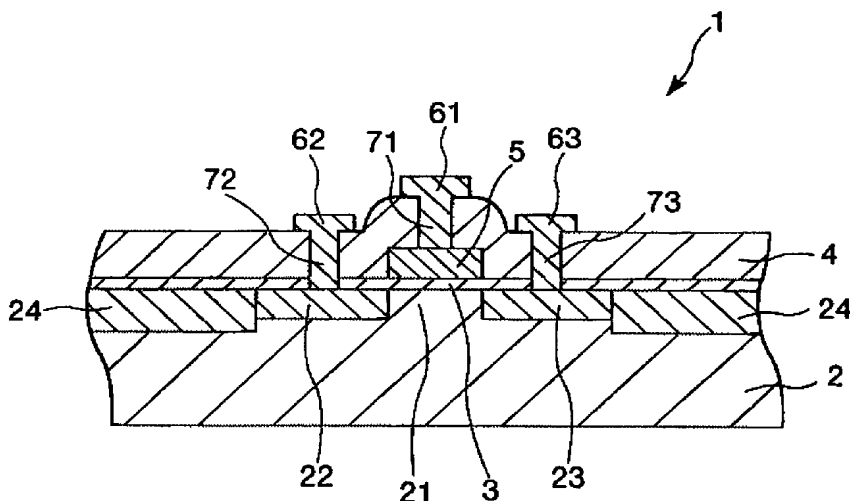
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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,
SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: A SEMICONDUCTOR DEVICE, AN ELECTRONIC DEVICE AND AN ELECTRONIC APPARATUS



(57) Abstract: A gate insulating film 3 is formed of an insulative inorganic material containing silicon and oxygen as a main material. The gate insulating film 3 contains hydrogen atoms. A part of the absorbance of infrared radiation of which wave number is in the range of 830 to 900 cm⁻¹ is less than both the absorbance of infrared radiation at the wave number of 830 cm⁻¹ and the absorbance of infrared radiation at the wave number of 900 cm⁻¹ when the insulating film to which an electric field has never been applied is measured by means of Fourier Transform Infrared Spectroscopy at room temperature. Further, in the case where the absolute value of the difference between the absorbance of infrared radiation at the wave number of 830 cm⁻¹ and the absorbance of infrared radiation at the wave number of 770 cm⁻¹ is defined as A and the absolute value of the difference between the absorbance of infrared radiation at the wave number of 900 cm⁻¹ and the absorbance of infrared radiation at the wave number of 990 cm⁻¹ is defined as B, then A and B satisfy the relation: A/B is 1.8 or more.



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Published:

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